Electronic Supplementary Information

Minute-made and low carbon fingerprint microwave synthesis of high quality templated mesoporous silica

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Sample	addition ^a	Preliminary	Ramp t	Plate	eau	Cooling ^b	Total ^c (min)	
		plateau	(min)	t	Т	bath T		
		T (°C)/t (min)		(min)	(°C)	(°C)		
MTM-01	S	none	20	40	130	RT	240	
MTM-02	F	60 /10	10	40	130	RT	180	
MTM-03	F	60/10	10	20	130	RT	160	
MTM-04	F	none	1	14	130	RT	125	
MTM-05	F	none	1	9	130	Ι	80	
a) $S = Slow$, drop wise addition followed by a 1 h stirring, $F = Fast$, addition on the edge of the beaker before								
putting the mixture in the autoclave, b) RT = Room Temperature, cooled at room temperature, I = Ice-bath,								
cooled in a ice-bath, c) Includes surfactant dissolution, heating and cooling before solid recovery.								

Table S1. Experimental conditions of the preliminary survey series of microwave syntheses.

Table S2. Q⁴ silicon proportion of selected silica materials.

Sample	δ (ppm) / Q ⁴ (%)
MTC-E-130	110.6 / 58.3
MTC-E-170	110.8 / 66.0
MTM-E-130	109.8 / 57.9
MTM-E-170	109.9 / 58.9





Figure S1. Diffraction patterns of several extracted silicas (x-axis is 2θ in degrees).



Figure S2. TEM pictures of MTM-01 silica.



Figure S3. Thermal effect on micelle swelling using Israelachvili model according to Tolbert et al. *Langmuir* **2005**, *21*, 470: a) dynamic long chain longitudinal shortening and transversal broadening, b) effect on micelle size.



Figure S4. SEM pictures of MTC-130 (a), MTM-130 (b), MTM-150 (c) and MTM-170 (d).



Figure S5. ²⁹Si HPDEC NMR spectra (black line), simulation (red line) and deconvolution (green dotted line) of classical and microwave materials. Q² percentage was omitted due to the lack of precision given by the fitting curve.



Figure S6. XRD Powder diagram of MTM-190-10 at low and large angles. The blue lines are at the scale given by the vertical axis and measured between 0.5 to 7 ° while the red lines are measured between 5 to 70° in 20 and reported with an intensity multiplied by 60. The narrow peak are diffraction due to the hexagonal phase as shown in Figure S1. The broad peak at 22° and 44° are typical of diffusion assigned to Si-Si distances in amorphous the SiO₂ phase of the channel wall.